

Substitute Form PTO-1449  
(Modified)U.S. Department of Commerce  
Patent and Trademark OfficeAttorney's Docket No.  
12406-059US2Application No.  
10/625,118**Information Disclosure Statement****by Applicant**

(Use several sheets if necessary)

(37 CFR § 1.98(b))

Applicant  
Volker HaerleFiling Date  
July 22, 2003Group Art Unit  
Unknown

2824

**U.S. Patent Documents**

Examiner Initial	Desig. ID	Document Number	Publication Date	Patentee	Class	Subclass	Filing Date If Appropriate
	AA						
	AB						
	AC						
	AD						
	AE						
	AF						
	AG						
	AH						
	AI						
	AJ						
	AK						

**Foreign Patent Documents or Published Foreign Patent Applications**

Examiner Initial	Desig. ID	Document Number	Publication Date	Country or Patent Office	Class	Subclass	Translation	
							Yes	No
	AL							
	AM							
	AN							
	AO							
	AP							

**Other Documents (include Author, Title, Date, and Place of Publication)**

Examiner Initial	Desig. ID	Document
BEO	AQ	Sugano, Hikaru, "Semiconductor Laser Manufacturing Method", October 27, 1989, pp. 1-6
	AR	
	AS	
	AT	

Examiner Signature

BETH E. OWENS

Date Considered

2.17.04

EXAMINER: Initials citation considered. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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BEO	AQ	B. Henle, et, al., "In Situ Selective Area Etching and Mowpe Regrowth Of GainsAs-InP ON InP Substrates," Int. Conf. On Indium Phosphide & Rel. Materials, U.S. NY, IEEE, Bd. CONF 4, S. pgs. 159-162
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Substitute Disclosure Form (PTO-1449)

Substitute Form PTO-1449 (Modified)  <b>Information Disclosure Statement by Applicant</b> (Use several sheets if necessary)  (37 CFR §1.98(b))	U.S. Department of Commerce Patent and Trademark Office	Attorney's Docket No. <b>12406-059US2</b>	Application No. <b>Unassigned</b>
	Applicant <b>Volker Haerle</b>		
	Filing Date <b>Herewith</b>	Group Art Unit Unknown <b>2824</b>	

U.S. Patent Documents							
Examiner Initial	Desig. ID	Document Number	Issue Date	Patentee	Class	Subclass	Filing Date If Appropriate
BE0	AA	4,415,404	11/15/1983	Riegl			
11	AB	4,614,564	09/30/1986	Sheldon et al.			
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Examiner Initial	Desig. ID	Document Number	Publication Date	Country or Patent Office	Class	Subclass	Translation	
							Yes	No
BE0	AK	0746011	10/2001	EP				
11	AL	0681315	06/2000	EP				
	AM	02-046407	02/1990	JP				
	AN	07202317	08/1995	JP				
BE0	AO	01270287	10/1989	JP with English Abstract			X	

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Examiner Initial	Desig. ID	Document
BE0	AP	JP-61 210687 Patent Abstracts of Japan, Venoffentlichung, September 8, 1986
BE0	AQ	G.B., Burns, "Lo-Temperature Native Oxide Removal From Silicon Using Nitrogen Trifluoride Prior To Low-Temperature Silicon Epitaxy", Appl. Phys. Lett. 53 (15), October 1988 pp 1423-1425
BE0	AR	T. Aoyama et al. "Silicon Surface Cleaning Using Photo excited Fluoring Gas Diluted With Hydrogen", J. Electrochem. Soc. Vol. 140, No. 6, June 1993 pp 1704-1708
BE0	AS	K. Ozasa et al., "Deposition Of Thin Indium Oxide Film and Its Application To Selective Epitaxy For In Situ Processing" Thin Solid Films, BD. 246, NR. 1/02, 1994, S. 58-64, XP000453839
BE0	AT	J.P. Harbison et al., "Tungsten Patterning As A Technique For Selective Area III-V MBE Growth", J. Vac. Sci. Technol. B3(2) March/April 1995

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Other Documents (include Author, Title, Date, and Place of Publication)		
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Beo	AU	JP 02-046407, Patent Abstracts of Japan, Veröffentlichung: February 2, 1990, Anmeldung: August 5, 1988
Beo	AV	S. Yoshida et al., "Selective-Area Epitaxy Of GaAs Using A New Mask Material For In Situ Processes", Inst. Phys. Conf. Ser. No. 129: Chapter 3, 1992, S-49-54, XP000366199
Beo	AW	P.J. Sullivan, et al., "Selective-Area Epitaxy For GaAs-on-InP Optoelectronic Integrated Circuits (OEICs)", Semiconductor Sci. & Technol. 8, No. 6, June 1993, pp 1179-1185
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Beo	AZ	Wong M. et al., "Characterization Of Wafer Cleaning And Oxide And Oxide Etching Using Vapor-Phase Hydrogen Fluoride"; June 1991, J. Electrochem, Soc., Vol. 138, No. 6, pp 1799-1802

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